

EAST - [10774400.wsp:1]

File View Edit Tools Window Help

Drafts
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 L1: (199) semiconductor and trench and r
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 L3: (1) 1 and (cobalt and alkylamine)
 L5: (2) 1 and (alkylamine)
 L4: (50) 1 and (cobalt)
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Plurals

Default operator: OR

Highlight all hit terms initially

1 and (cobalt)

OK Cancel Image Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6740580 B1	20040525	10	Method to form copper interconnects by adding an aluminum layer to the copper	438/627	438/618; 438/628;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6727175 B2	20040427	13	Method of controlling metal formation processes using ion implantation, and	438/659	438/677; 438/678;
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6724087 B1	20040420	9	Laminated conductive lines and methods of forming the same	257/762	257/751
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6717268 B2	20040406	9	Electromigration-reliability improvement of dual damascene interconnects	257/758	257/767; 257/773
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6717189 B2	20040406	16	Electroless plating liquid and semiconductor device	257/200	106/1.11; 106/1.23;
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6716330 B2	20040406	16	Electroless plating apparatus and method	205/81	204/232
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6689689 B1	20040210	10	Selective deposition process for allowing damascene-type Cu interconnect lines	438/687	438/658; 438/660
8	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6677233 B2	20040113	10	Material deposition from a liquefied gas solution	438/658	257/E21.175; 257/E21.586;
9	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6671947 B2	20040106	19	Method of making an interposer	29/846	257/686; 257/E23.011;
10	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6664192 B2	20031216	14	Method for bottomless deposition of barrier layers in integrated circuit metallization	438/704	257/E21.171; 257/E21.579;
11	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6642146 B1	20031104	26	Method of depositing copper seed on semiconductor substrates	438/687	438/622; 438/624;